

#### Silicon Carbide Schottky Barrier Rectifier diode in bare die form

### Rev 1.0 30/10/23

## Features:

- Capable of high temperature operation >= 175°C
- High Frequency Operation
- High Surge Current Capability
- No Reverse Recovery / No Forward Recovery
- Positive Temperature Coefficient

# Ordering Information:

The following part suffixes apply:

- No suffix MIL-STD-750 /2073 Visual Inspection
- "H" MIL-STD-750 /2073 Visual Inspection + MIL-PRF-38534 Class H LAT
- "K" MIL-STD-750 /2073 Visual Inspection + MIL-PRF-38534 Class K LAT

LAT = Lot Acceptance Test.

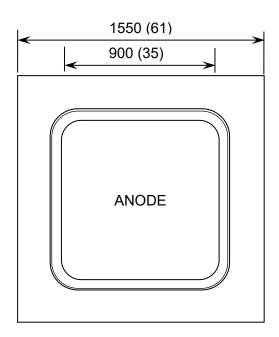
For further information on LAT process flows see below.

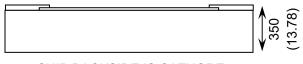
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# Supply Formats:

- Default Die in Waffle Pack (400 per tray capacity)
- Sawn Wafer on Tape By specific request
- Unsawn Wafer By specific request
- With additional electrical selection By specific request

## Die Dimensions in µm (mils)





CHIP BACKSIDE IS CATHODE

# **Mechanical Specification**

Die Size (Unsawn)	1550 x 1550 61 x 61	µm mils	
Anode Pad Size	900 x 900 35 x 35	µm mils	
Die Thickness	350 (±20) 13.78 (0.79)	µm mils	
Top Metal Composition	Al 4µm		
Back Metal Composition	Ag 0.4µm		





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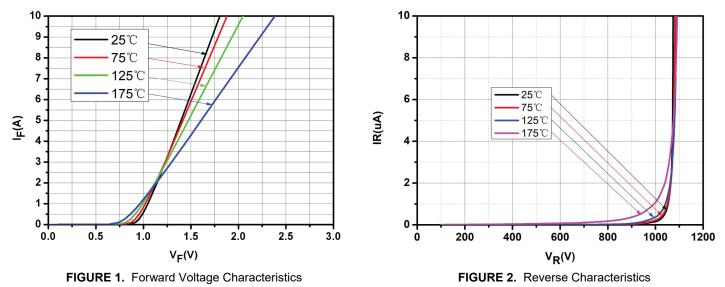
PARAMETER	SYMBOL	VALUE	UNIT		
Repetitive peak reverse voltage	V <sub>RRM</sub>	650	V		
Surge peak reverse voltage	V <sub>RSM</sub>	650	V		
DC Peak Blocking Voltage	V <sub>BR</sub>	650	V		
Average forward rectified current	I <sub>F(AV)</sub>	6	А		
Repetitive Peak Forward Surge Current	I <sub>FRM</sub>	30	А		
Peak Single-Cycle Non-Repetitive Surge Current	I <sub>FSM</sub>	70	А		
Operating Junction temperature	TJ	-55 to 175	°C		
Storage Temperature Range	T <sub>STG</sub>	-65 to 175	°C		

### Electrical Characteristics T<sub>J</sub> = 25°C unless otherwise stated

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
Maximum instantaneous forward voltage <sup>1</sup>	V <sub>F1</sub>	V <sub>RRM</sub> = 650V, I <sub>FM</sub> = 6A	-	1.50	1.70	V
	V <sub>F2</sub>	V <sub>RRM</sub> = 650V, I <sub>FM</sub> = 6A, T <sub>J</sub> = 175°C	-	1.75	2.20	v
Maximum reverse leakage current <sup>1</sup>	I <sub>RM</sub> @ V <sub>RM</sub>	V <sub>R</sub> = 650V	-	0.03	3	μΑ
		V <sub>R</sub> = 650V, T <sub>J</sub> = 175°C	-	0.6	25	
Junction Capacitance	CT	V <sub>R</sub> = 0V, f = 1MHz,	-	382	-	pF
Reverse Recovery Charge	Q <sub>C</sub>	$V_R$ = 400V , I <sub>F</sub> = 6A, di/dt = 200A/µs	-	23.8	-	nC
Capacitance Stored Energy	Ec	V <sub>R</sub> = 400V	-	5.88	-	μJ

**1.** Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2.0%

### Typical Characteristics $T_J = 25^{\circ}C$ unless otherwise stated

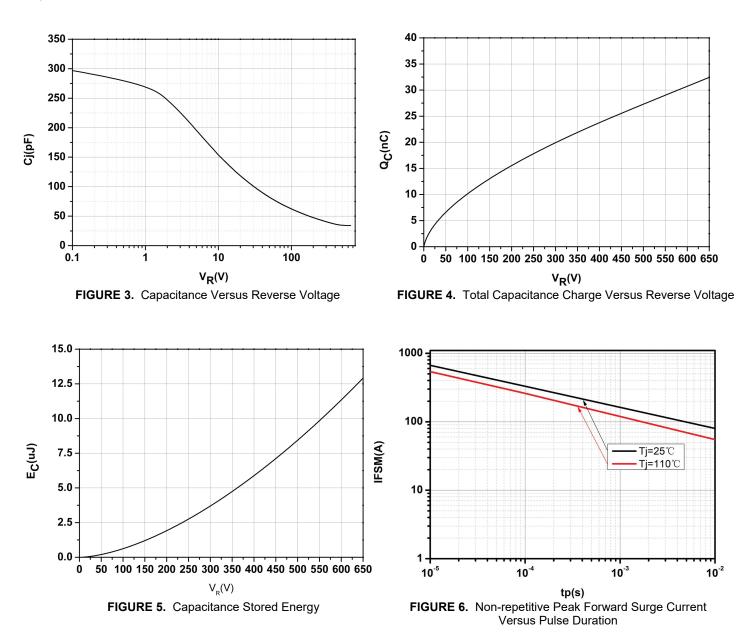






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